

# Unit 1

## Design Rules and Stick Diagrams

# Stick Diagrams

- VLSI design aims to translate circuit concepts onto silicon
- stick diagrams are a means of capturing topography and layer information - simple diagrams
- Stick diagrams convey layer information through colour codes (or monochrome encoding)
- Used by CAD packages, including Microwind

# Design Rules

- Allow translation of circuits (usually in stick diagram or symbolic form) into actual geometry in silicon
- Interface between circuit designer and fabrication engineer
- Compromise
  - designer - tighter, smaller
  - fabricator - controllable, reproducible

# Lambda Based Design Rules

- Design rules based on single parameter,  $\lambda$
- Simple for the designer
- Wide acceptance
- Provide feature size independent way of setting out mask
- If design rules are obeyed, masks will produce working circuits
- Minimum feature size is defined as  $2\lambda$
- Used to preserve topological features on a chip
- Prevents shorting, opens, contacts from slipping out of area to be contacted

# Design Rules - The Reality

- Manufacturing processes have inherent limitations in accuracy and repeatability
- Design rules specify geometry of masks that provide reasonable yield
- Design rules are determined by experience

# Problems - Manufacturing

- Photoresist shrinking / tearing
- Variations in material deposition
- Variations in temperature
- Variations in oxide thickness
- Impurities
- Variations between lots
- Variations across the wafer

# Problems - Manufacturing

- Variations in threshold voltage
  - oxide thickness
  - ion implantation
  - poly variations
- Diffusion - changes in doping (variation in R, C)
- Poly, metal variations in height and width -> variation in R, C
- Shorts and opens
- Via may not be cut all the way through
- Undersize via has too much resistance
- Oversize via may short

# Meta Design Rules

- Basic reasons for design rules
- Rules that generate design rules
- Under worst case misalignment and maximum edge movement of any feature, no serious performance degradation should occur



# VLSI DESIGN RULES

$$\lambda = 1\mu m$$

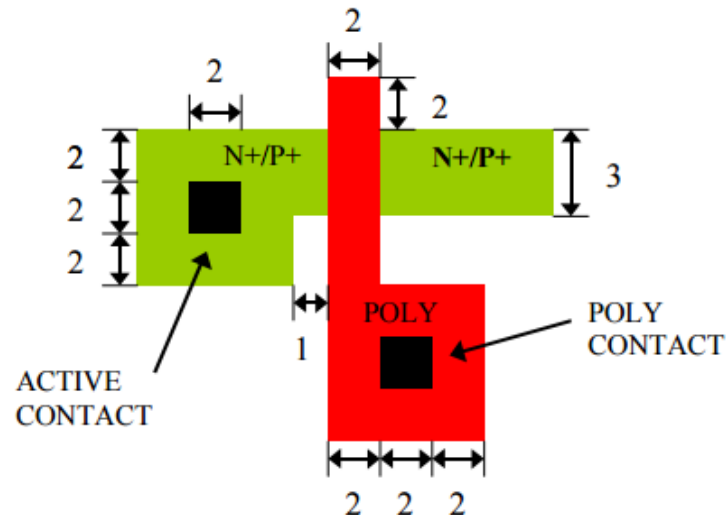
## MINIMUM WIDTH AND SPACING RULES

LAYER	TYPE OF RULE	VALUE
POLY	Minimum Width	$2\lambda$
	Minimum Spacing	$2\lambda$
ACTIVE	Minimum Width	$3\lambda$
	Minimum Spacing	$3\lambda$
NSELECT	Minimum Width	$3\lambda$
	Minimum Spacing	$3\lambda$
PSELECT	Minimum Width	$3\lambda$
	Minimum Spacing	$3\lambda$
METAL1	Minimum Width	$3\lambda$
	Minimum Spacing	$3\lambda$

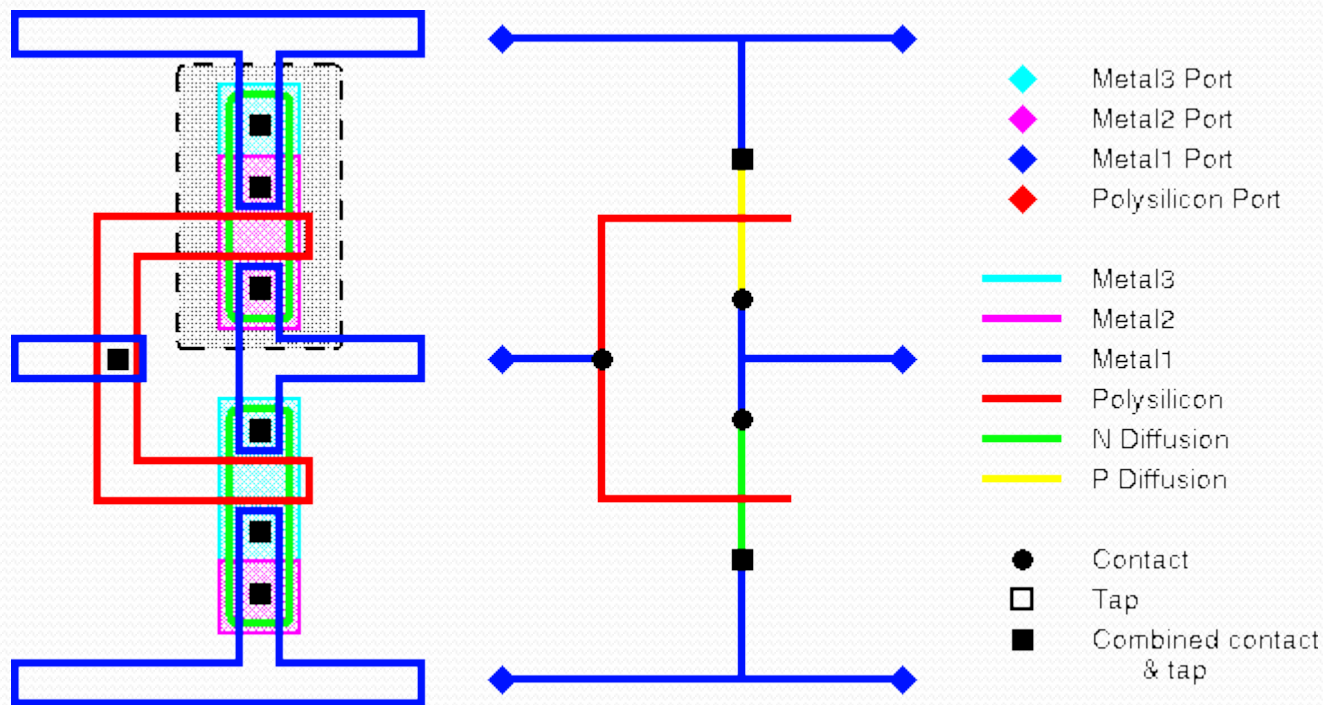
# VLSI DESIGN RULES (Contd.)

## MOSFET LAYOUT RULES

RULE	MEANING	VALUE
POLY Overlap	Minimum extension over ACTIVE	$2\lambda$
POLY-ACTIVE	Minimum Spacing	$1\lambda$
MOSFET Width	Minimum N+/P+ MOSFET W	$3\lambda$
ACTIVE CONTACT	Exact Size	$2\lambda \times 2\lambda$
	Minimum Space to ACTIVE Edge	$2\lambda$
POLY CONTACT	Exact Size	$2\lambda \times 2\lambda$
	Minimum Space to POLY Edge	$2\lambda$

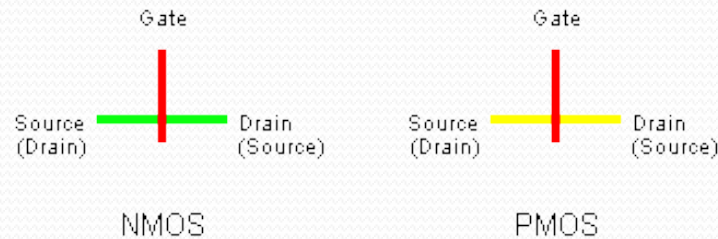


# Stick Diagram and Mask Layout Design of CMOS Inverter



- **Transistors**

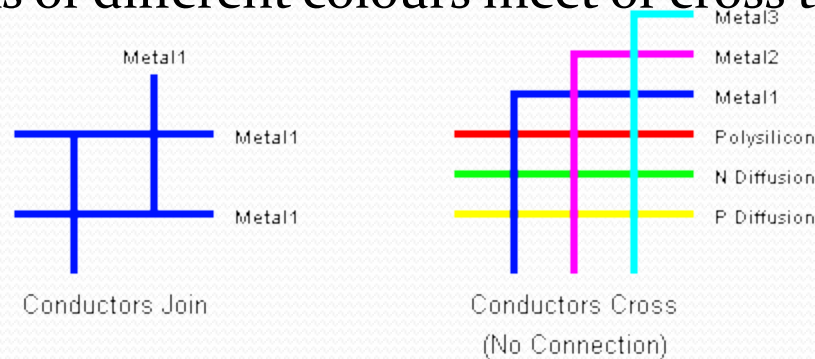
- A transistor exists where a polysilicon stick crosses either an N diffusion stick (NMOS transistor) or a P diffusion stick (PMOS transistor).



- There is no difference in the construction of a transistor source and a transistor drain. The source is determined as the source of conductors (electrons for NMOS / holes for PMOS) when current flows through the channel. In some pass transistor circuits, the source and drain may swap over during use.

- **Implied Connections and Crossovers:**

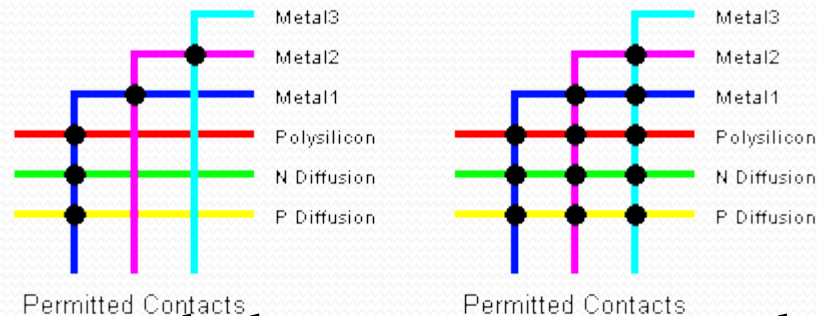
- Where two sticks of the same colour meet or cross there is always a connection.
- Where two sticks of different colours meet or cross there is no implied connection.



- N and P diffusions may not cross each other. Where poly crosses diffusion we have a transistor.

- **Contacts**

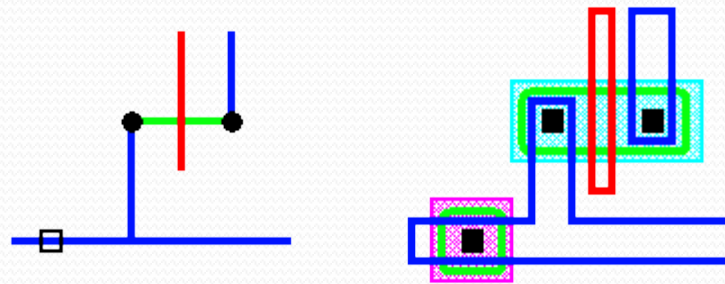
- A connection may be explicitly defined using a filled black circle. In the general case a connection is permitted where the mask layers will be separated by just one layer of insulator (through which a "contact cut" may be defined). Thus P diffusion may connect to Metal1 but not directly to Metal2.



- In a process where stacked contacts are permitted, we may draw a contact between non-adjacent conductors; e.g. between Poly and Metal3, in which case the connection to intermediate layers (Metal1 and Metal2) is implied.

- **Taps**

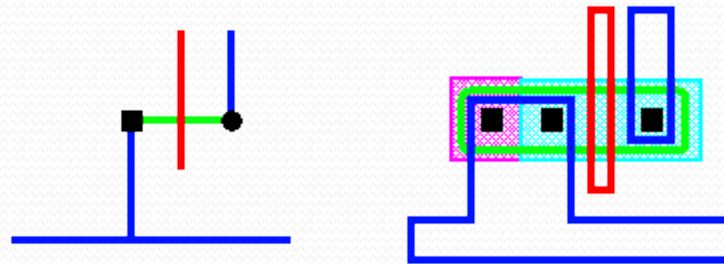
- The tap represents a connection to something we can't see; either the N-Well (not shown on our stick diagram) or the wafer substrate. A tap is defined using an unfilled black square. Here there will be only one conductor crossing the square (Metal1 power or ground rail).



- An N-Well Tap is inferred where the connection is from a power rail while a Substrate Tap is inferred where the connection is from a ground rail.

- **Combined Contacts & Taps**

- We can often save space by using a combined contact and tap. Here the tap shares the same Active Area as the contact. A combined contact and tap is defined using a filled black square in place of the source contact (filled black circle).



- A combined contact and tap can only be used where the end of a diffusion stick coincides with a contact to the power or ground rail.



- **Stick Diagram Colour Code**

P diffusion	:	Yellow/Brown		Metal <sub>1</sub>	:	Blue
N diffusion	:	Green		Metal <sub>2</sub>	:	Magenta/Purple
Polysilicon	:	Red		Metal <sub>3</sub>	:	Cyan/L.Blue
Contacts & Taps	:	Black				

- In case of deviation from these colours, there is a need to include a key with your stick diagram.

# Advantages of Generalised Design Rules

- Ease of learning because they are scalable, portable, durable
- Longevity of designs that are simple, abstract and minimal clutter
- Increased designer efficiency
- Automatic translation to final layout